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# ABSTRACT OF THE DISCLOSURE

A semiconductor device has a gate electrode formed extending on a first and second gate insulation films formed on P type semiconductor substrate, an N+ type source region adjacent to one end of the gate electrode, an N-type drain region facing said source region through a channel region, having high impurity concentration peak at a position of the predetermined depth at least in said substrate under said first gate insulation film, and formed so that high impurity concentration becomes low at a region near surface of the substrate, an N- type drain region formed so as to range to the N- type drain region, an N+ type drain region separated from the other end of said gate electrode and included in said N- type drain region, and an N type layer formed so as to span from one end portion of said first gate insulation film to said N+ type drain region.